IN THE CLAIMS

The pending claims are as follows:

1. (Previously Amended) A method comprising:

introducing an etch stop layer directly over a substrate;

introducing a base layer over the etch stop layer;

introducing a dielectric cap layer over the base layer between an interconnection line and a contact point on the substrate, the dielectric cap layer comprising a plurality of different material layers, wherein each respective layer of the plurality of different material layers is selectively etchable with respect to the etch stop layer;

introducing a photoimageable material over the dielectric cap layer; and

patterning an interconnection to the contact point.

2. (Original) The method of claim 1, wherein patterning an interconnection to the contact point comprises patterning an interconnection directly to a device on the substrate.

3. (Previously Amended) The method of claim 2, wherein introducing the dielectric cap layer comprises introducing a plurality of alternating material layers.

4. (Previously Amended) The method of claim 3, wherein the introducing the dielectric cap layer comprises introducing silicon dioxide as an ultimate layer.

5. (Original) The method of claim 4, wherein introducing a plurality of alternating material layers comprises alternating silicon dioxide layers with at least one other material layers.

6. (Original) The method of claim 5, wherein the number of alternating silicon dioxide layers comprises at least six.

7. (Previously Amended) The method of claim 1, wherein the dielectric cap layer comprises a first dielectric layer, the method further comprising introducing a second dielectric layer between the first dielectric layer and the etch stop layer.

8. (Previously Amended) A method comprising:

introducing an etch stop layer directly over a substrate;

introducing a dielectric layer over the etch stop layer between an interconnection line and a contact point on the substrate, the dielectric layer comprising a plurality of alternating material layers; and

patterning an interconnection to the substrate.

9. (Original) The method of claim 8, wherein the interconnection line comprises a first level interconnection line.

10. (Previously Amended) The method of claim 9, wherein introducing a plurality of alternating material layers comprises introducing silicon dioxide as an ultimate material layer.

11. (Original) The method of claim 10, wherein introducing a plurality of alternating material layers comprises alternating silicon dioxide layers with at least one other material layers.

12. (Original) The method of claim 11, wherein the number of alternating silicon dioxide layers comprises at least six.

13. (Original) The method of claim 8, wherein the dielectric layer comprises a first dielectric layer, the method further comprising introducing a second dielectric layer between the first dielectric layer and the substrate.

14 - 17 (Withdrawn)

18. (Previously Added) The method of claim 1, further comprising introducing a photoimageable material layer, wherein the dielectric layer comprising the plurality of different material layers is introduced between the substrate and the photoimageable material layer.

19. (Canceled)

20. (Previously Amended) The method of claim 1, wherein the dielectric layer comprising the plurality of different material layers is introduced between the etch stop layer and the photoimageable material layer.

21. (Previously Added) The method of claim 8, further comprising introducing a photoimageable material layer, wherein the dielectric layer comprising the plurality of alternating material layers is introduced between the substrate and the photoimageable material layer.

22. (Canceled)

23. (Previously Amended) The method of claim 8, wherein the dielectric layer comprising the plurality of alternating material layers is introduced between the etch stop layer and a photoimageable material layer.

24. (Previously Added) The method of claim 1, wherein the etch stop layer is silicon nitride.

25. (Previously Added) The method of claim 8, wherein the etch stop layer is silicon nitride.

26. (Previously Added) The method of claim 1, wherein the plurality of different material layers includes at least one layer of silicon oxynitride.

27. (Previously Added) The method of claim 8, wherein the plurality of alternating material layers comprises alternating silicon oxynitride layers with at least one other material layer.

28. (Previously Added) A method comprising:

forming a planarized base layer over a substrate having a plurality of devices;

forming a dielectric cap layer over the base layer, wherein the dielectric cap layer is formed by alternating a first material layer and a second material layer having a higher dielectric constant than the first material layer, wherein the first material layer is more than five times thicker than the second material layer; and

patterning an interconnection to a contact point.

29. (Previously Added) The method of claim 28, wherein the base layer is doped with phosphorous or boron to serve as a collector of metallic contaminants.